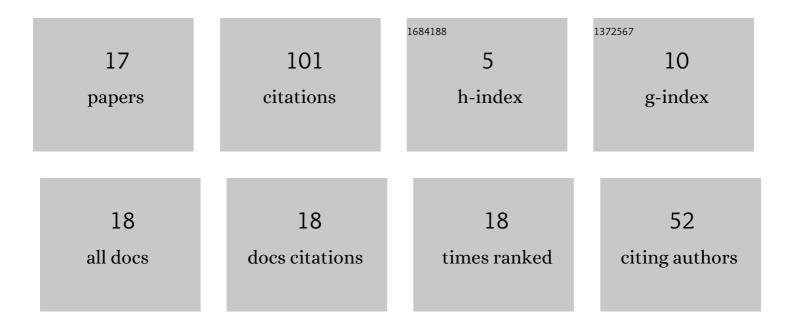
Johann Cervenka

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	A deterministic Wigner approach for superposed states. Journal of Computational Electronics, 2021, 20, 2104.	2.5	2
2	Numerical constraints and non-spatial open boundary conditions for the Wigner equation. Journal of Computational Electronics, 2021, 20, 2052-2061.	2.5	5
3	Numerical Solution of the Constrained Wigner Equation. , 2020, , .		1
4	TCAD simulation of tunneling leakage current in CaF2/Si(111) MIS structures. Current Applied Physics, 2015, 15, 78-83.	2.4	4
5	Modeling of deep-submicron silicon-based MISFETs with calcium fluoride dielectric. Journal of Computational Electronics, 2014, 13, 733-738.	2.5	5
6	Applicability of Macroscopic Transport Models to Decananometer MOSFETs. IEEE Transactions on Electron Devices, 2012, 59, 639-646.	3.0	4
7	Strained MOSFETs on ordered SiGe dots. Solid-State Electronics, 2011, 65-66, 81-87.	1.4	2
8	The Effect of Microstructure on Electromigration-Induced Failure Development. ECS Transactions, 2009, 23, 345-352.	0.5	2
9	Electromigration failure development in modern dual-damascene interconnects. , 2009, , .		0
10	A Comprehensive TCAD Approach for Assessing Electromigration Reliability of Modern Interconnects. IEEE Transactions on Device and Materials Reliability, 2009, 9, 9-19.	2.0	47
11	The Effect of Copper Grain Size Statistics on the Electromigration Lifetime Distribution. , 2009, , .		5
12	Parameter modeling for higher-order transport models in UTB SOI MOSFETs. Journal of Computational Electronics, 2008, 7, 168-171.	2.5	3
13	Three-dimensional simulation of sacrificial etching. Microsystem Technologies, 2008, 14, 665-671.	2.0	0
14	A 2D non-parabolic six-moments model. Solid-State Electronics, 2008, 52, 1606-1609.	1.4	5
15	Consistent higher-order transport models for SOI MOSFETs. , 2008, , .		1
16	Quantum correction for DG MOSFETs. Journal of Computational Electronics, 2007, 5, 397-400.	2.5	9
17	A Study of Boron Implantation into High Ge Content SiGe Alloys. ECS Transactions, 2006, 3, 667-676.	0.5	2